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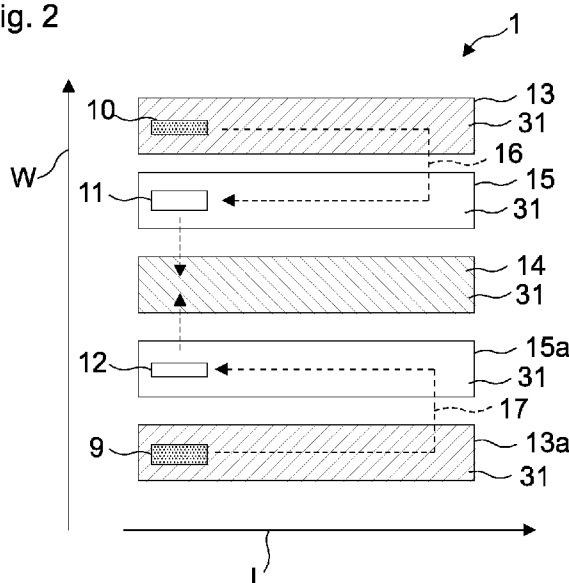
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(54) Title: POWER SEMICONDUCTOR MODULE COMPRISING SWITCH ELEMENTS AND DIODES

Fig. 2



(57) Abstract: A power module (1) comprises a first switch (2) comprising a first switch element (9) and an associated first diode (10), a second switch (3) comprising a second switch element (11) and an associated second diode (12), the first and second switches (2, 3) being electrically connected to form a half-bridge, wherein the switch elements (9, 11) and diodes (10, 12) are located next to each other, wherein the second switch element (11) and second diode (12) are located between the first switch element (9) and the first diode (10).

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Description

POWER SEMICONDUCTOR MODULE COMPRISING SWITCH ELEMENTS AND DIODES

5 The present disclosure relates to a power module comprising first and second switches, each switch comprising at least one switch element and an associated diode. The switches are connected to form a half-bridge. A half-bridge is an electric circuit comprising two switches connected in series between a
10 DC+ and DC- terminal, wherein an AC terminal is connected between the switches. The switch connected to the DC+ terminal is denoted as high side (HS) switch, the switch connected to the DC- terminal is denoted as low side (LS) switch.

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Half-bridge power modules form the key building blocks in various power electronic devices, such as motor drives or power converters which can be used in electric vehicles (EV). Power modules need to be compact and designed to operate in
20 harsh environments for a long period of time. The power modules may comprise silicon (Si), silicon carbide (SiC), gallium nitride (GaN) or other semiconductor elements. Three half-bridge power modules form a so-called six-pack power module, forming the three phases of an inverter. The
25 electromagnetic design of the switches is crucial for exploiting the fast switching capabilities of the device.

Documents WO 2010/004802 A1 and WO 2013/171996 A1 disclose different power module layouts. Document EP 3 246 945 A1
30 discloses a power module with three DC terminals arranged with alternating polarity for reducing the contribution of the terminals to stray inductance of the power module.

Document JP 2005 216876 A discloses a power module with an arrangement of high side and low side IGBTs and diodes such that wires are arranged in parallel and wiring inductances are reduced by electric currents flowing in a reverse
5 direction. Documents EP 3 613 077 B1 and US 2011/062491 A1 disclose further half-bridge power modules.

Embodiments of the disclosure relate to a power module with improved electromagnetic properties.

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According to an embodiment, a power module comprises a first switch comprising a first switch element and an associated first diode and comprises a second switch comprising a second switch element and an associated second diode. Each of the
15 switch elements is electrically connected in parallel to its associated diode. The first and second switches are electrically connected to form a half-bridge. The switch elements and diodes are located next to each other, wherein the second switch element and second diode may be located
20 between the first switch element and the first diode.

The power module may be a Si, or a wide-bandgap module such as a SiC or GaN module, for example. The switch elements may be insulated gate bipolar transistors (IGBT), as an example.
25 The switch elements may be alternatively MOSFET or MISFET transistors, for example. The associated diodes may be free-wheeling diodes (FWD). A switch element is electrically connected with its associated diode such that the associated diode is connected between collector and emitter of the
30 switch element. In this way, current can be conducted via the diode in one direction.

In an embodiment, the first switch is an HS switch, connected to a DC+ terminal. The first switch element and the first

diode are in this case called HS switch element and HS diode, respectively. The second switch is an LS switch, connected to a DC- terminal. The second switch element and the second diode are in this case called LS switch element and LS diode, respectively.

In an alternative embodiment, the first switch is an LS switch and the second switch is an HS switch.

The arrangement of the switch elements and diodes next to each other in the specified order is symmetric in the sense that the order of sides to which the components are attributed is the same in both directions. This enables reducing stray inductance. Furthermore, also the lengths of commutation paths between a switch element, the diode of the other side and a DC terminal can be confined, which reduces the inductance of loop currents.

In an embodiment, the first switch element is located next to the second diode and the first diode is located next to the second switch element. Accordingly, the switches and diodes of different sides are located next to each other, leading to short commutation paths. In some embodiments, the second switch element is arranged closer to the first diode than the associated second diode.

The power module may comprise at least three DC terminals located on the same side of the power module, wherein the DC terminals have alternating polarity. As an example, the layout of the terminals may be DC+/DC-/DC+. Alternatively, the layout of the terminals may be DC-/DC+/DC-. It is also possible that the power module has further DC terminals of alternating polarity on the same side. The power module may

comprise an AC terminal located on a side opposite to the DC terminals.

The power module may comprise metallizations. The metallizations may be in the form of DC+, DC- and AC metallizations connected to the respective terminals. The switch elements and diodes may be located on the DC+ and AC metallizations. The metallizations may be arranged in the form of strips parallel to each other.

10

In embodiments, each of the first and second switches comprises several switch elements and associated diodes connected in parallel to other switch elements and associated diodes of the same switch. Each of the switches may comprise an odd number of switch elements and associated diodes. As an example, each of the switches may comprise three switch elements and associated diodes.

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The power module may have a highly symmetric layout. As an example, the switch elements of the same switch may be located in a row. The switch elements may be located at regular distances. Also the associated diodes of the same switch may be located in a row. Each of the switch elements of the same switch may be located on the same metallization. Also each of the associated diodes may be located on the same metallization.

20

25

In embodiments, the power module comprises additional first switch elements, associated additional first diodes, additional second switch elements and associated additional second diodes, located in the same column as the first and second switch elements and associated diodes. The additional switch elements and diodes may be arranged in the same order as the first and second switch elements and diodes. The

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additional switch elements and diodes can also be arranged in an opposite order than the first and second switch elements and diodes. The additional first and second switch elements and associated diodes may be electrically connected in
5 parallel to the first and second switch elements and associated diodes.

Accordingly, the pattern of switch elements and diodes is repeated along the column. In addition to that, the switches may comprise further switch elements and diodes arranged in
10 the same row of first and second switch elements and diodes.

The present disclosure comprises several embodiments. Every feature described with respect to one of the embodiments is also disclosed herein with respect to the other embodiment, even if the respective feature is not explicitly mentioned in
15 the context of the specific embodiment.

Further features, refinements and expediciencies become apparent from the following description of the exemplary embodiments in connection with the figures. In the figures,
20 elements of the same structure and/or functionality may be referenced by the same reference signs. It is to be understood that the embodiments shown in the figures are illustrative representations and are not necessarily drawn to scale.

25

Figure 1 is a schematic circuit diagram of a power module in form of a half bridge,

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Figure 2 is a schematic view of a power module according to an embodiment,

Figure 3 is a top view of a power module according to the layout of Figure 2,

Figure 4 is a detailed view of a gate metallization layout
5 of the embodiment of Figure 3,

Figure 5 is a detailed view of an alternative gate metallization layout for the embodiment of Figure 3,

10 Figures 6, 7, 8, 9 are schematic views of power modules according to further embodiments.

Figure 1 shows a schematic circuit diagram of a power module 1 in form of a half bridge. The power module 1 may be used in
15 a motor drive or power converter in an electric vehicle, for example.

The power module 1 comprises a first switch 2 and a second switch 3 connected in series between two DC+/- terminals 4, 5
20 with an AC terminal 6 connected between the switches 2, 3. When providing a voltage between the DC+/- terminals 4, 5 and alternately switching on and off the switches 2, 3 at gate terminals 7, 8, an AC voltage is generated at the AC terminal 6.

25

The first switch 2 comprises a first switch element 9 and an associated first diode 10. The first diode 10 is connected between an emitter and a collector of the first switch element 9. The second switch 3 comprises a second switch
30 element 11 and an associated second diode 12, which is connected between an emitter and a collector of the second switch element 11. The switch elements 9, 11 may be insulated-gate bipolar transistors (IGBT). The diodes 10, 12

may be free-wheeling diodes (FWD). The first switch 2 is in this case directly connected to the DC+ terminal and is also called "high side" (HS) switch. The first diode 10 and the first switch element 9 are called HS diode 10 and HS switch
5 element 9, respectively. The second switch 3 is in this case directly connected to the DC- terminal and is also called "low side" (LS) switch. The second diode 11 and the second switch element 12 are called LS diode and LS switch element, respectively.

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It is also possible that the first switch 2 comprises one or more further first switch elements 9' and associated further first diodes 10' connected in parallel to the first switch element 9 and associated first diode 10 and the second switch
15 3 comprises one or more further second switch elements 11' and one or more associated further second diodes 12' connected in parallel to the second switch element 11 and the associated second diode 12.

20 The one or more further first switch elements 9' may have the same features as the first switch element 9. The same applies for the further second switch elements 11', further first diodes 10' and further second diodes 12' in relation to the second switch element 11, first diode 10 and second diode 12,
25 respectively. The first switch element 9 and further first switch elements 9' are also denoted as first switch elements 9, 9', the second switch element 11 and the further second switch elements 11' are also denoted as second switch elements 11, 11' in the following. The first diode 10 and
30 further first diodes 10' are also denoted as first diodes 10, 10', and the second diode 12 and the further second diodes 12 are also denoted as second diodes 12, 12' in the following.

As an example, an odd number of first switch elements 9, 9' and associated diodes 10, 10' may be connected in parallel and an odd number of second switch elements 11, 11' and associated second diodes 12, 12' may be connected in parallel.

During switching, commutation loop currents flow between the first switch 2 and the second switch 3 and the associated commutation loop inductance impacts the switching speed.

Figure 2 shows an embodiment of a layout scheme of a power module 1 comprising a half-bridge in accordance with the circuit diagram of Figure 1. Only first and second switch elements 9, 11 and associated diodes 10, 12 are depicted. The Further first and second switch elements can be present in a corresponding arrangement shifted along a length direction L.

The switch elements 9, 11 and associated diodes 10, 12 are located on metallizations 31 on a substrate. The metallizations 31 can also be denoted as "traces". In particular, the first switch element 9 and the first diode 10 are located on DC+ metallizations 13, 13a and the second switch element 11 and the second diode 12 are located on AC metallizations 15, 15a. In the shown embodiment, the first switch element 9 and the first diode 10 are the HS switch element and HS diode, respectively. The second switch element 11 and the second diode 12 are the LS switch element and LS diode, respectively.

The switch elements 9, 11 and associated diodes 10, 12 are arranged next to each other in the order: first switch element 9 - second diode 12 - first diode 10 - second switch element 12 (in Figure 2 from bottom to top). As can be seen

in Figure 2, between two components located "next" to each other no other switch element or diode is located. The order of the sides of the components (HS-LS-LS-HS) is the same when going from bottom to top or from top to bottom. The elements
5 are arranged in a column along a width direction W of the power module 1. The elements located in the column at least overlap along the length direction L or are arranged centered to each other.

10 In this arrangement, the first switch element 9 is not located adjacent to the associated first diode 10. Instead, the first switch element 9 and the second diode 12 are located as a pair close to each other and the second switch
15 element 11 and the first diode 10 are located as a pair close to each other. Thus, the switch elements 9, 11 and diodes 10, 11 of different sides are spatially clustered as pairs. This has the effect that a current commutation path 16 from the first diode 10 via the second switch element 11 to a DC-
20 metallization 14 is spatially well defined and confined. Also a current commutation path 17 from the first switch element 9 via the second diode 12 to the DC- metallization 14 is spatially well defined and confined. Thereby, the inductance of the commutation loops is minimized.

25 The two DC+ metallizations 13, 13a are on the same electric potential but may be connected to separate terminals. The two AC metallizations 15, 15a are on the same AC potential. The AC metallizations 15, 15a may be connected to a single
30 terminal.

Figure 3 shows a top view of an embodiment of a power module 1 with the layout scheme of Figure 2 arranged on a substrate 18.

In the shown embodiment, three first diodes 10, 10', 10'' are located next to each other on the same DC+ metallization 13, associated to three first switch elements 9, 9', 9'' located
5 next to each other on the further DC+ metallization 13a.

Three second diodes 12, 12', 12'' are located next to each other on the same AC metallization 15, associated with three second switch elements 11, 11', 11'' located next to each other on the same, further AC metallization 15a. Accordingly,

10 the embodiment has three switch elements and associated diodes per side. The switch elements and associated diodes are located at regular distances only shifted relative to each other along the length direction L. The diodes and switch elements of each side are located next to each other
15 along a length direction L on the same metallization, corresponding to a parallel connection of several first switches and a parallel connection of several second switches in the circuit diagram of Figure 1. The shown arrangement of diodes and switch elements is very regular and, thereby, a
20 balanced distribution of loads and losses for the diodes and switch elements can be achieved.

While the layout scheme shows three diodes and switch elements per side located on the same metallization, more or
25 less than three diodes per side may be present. In embodiments, only a single diode and a single switch element per side may be present.

The AC metallizations 15, 15a are connected to a single AC
30 terminal 6. The DC+ metallizations are connected to two separate DC+ terminals 4, 4' instead of the single terminal 4 shown in Figure 1. The DC+ terminals 4, 4' enclose a DC-

terminal 5 and are located at a side opposite than the AC terminal 6.

Each of the switch elements 9, 9', 9'', 11, 11', 11'' and
5 each of the diodes 11, 11', 11'' and 12, 12', 12'' is
connected to an adjacent DC+, DC- or AC metallization 13,
13a, 14, 15, 15a, by wire bonds 19. In this embodiment, also
the wire bonds 19 are homogeneously directed along the width
direction W. Overall, a very lean layout of metallizations
10 and connection structures is achieved. Thereby, the chip
placement area can be maximized and heat spreading can be
increased.

Figure 4 shows in a detailed view of a gate metallization
15 layout of the embodiment of Figure 3. The position of the
detailed view is indicated in Figure 3 by dashed lines.

Gates 20, 20', 20'' of the second switch elements 11, 11',
11'' are connected to a gate metallization 21 arranged
20 between the first DC+ metallization 13 and the first AC
metallization 15. As can be seen from Figure 3, the gates of
the first switch elements 9, 9', 9'' are connected to a
second gate metallization 22 located between the second DC+
metallization 13a and an edge of the substrate 18. Depending
25 on the overall layout, the second gate metallization 22 may
be alternatively located between the second DC+ metallization
13a and the second AC metallization 15a, corresponding to the
position of the first gate metallization 21. As can be seen,
a very lean layout of gate metallizations is achieved.

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Figure 5 shows in a detailed view an example of an
alternative gate metallization layout which can be embodied
in the power module 1 of Figure 3 instead of the gate

metallization layout shown in Figure 4. In Figure 5, the first gate metallization 21 is located on the DC- metallization. As in Figure 4, the first gate metallization 21 is in the form of an elongate strip, arranged in parallel to the DC+, DC- and AC metallizations.

Figures 6, 7, 8 and 9 show further layouts of embodiments of power modules 1.

Figure 6 shows a layout of a power module 1, in which, compared to Figure 3, the locations of the second switch element 11 and the second diode 12 have been swapped. Also in this case, the arrangement of the diodes and switches along the length direction L is homogenous. Thereby, a balanced distribution of loads and losses for the diodes and switches within the sides is achieved.

In contrast to the embodiment of Figure 2, the switch elements 9, 11 of different sides are arranged close to each other and the diodes 10, 12 of different sides are arranged close to each other. The switch elements 9, 11 are arranged at a distance from the associated diodes 10, 12. The pairs of switch elements 9, 11 are separated by an AC metallization 15 from the pairs of the diodes 10, 12.

The metallizations 13, 13a, 14, 15, 15a are elongated strips arranged parallel to each other in a single row. Also here, in case of several switches per side, the further sets of switch elements and diodes of the switches are positioned on along the respective metallization at regular distances in a row, i.e., along the length direction L.

The switch elements 9, 11 can be connected to gate metallizations arranged adjacent to the AC metallization 15 and DC+ metallization 13, respectively. As an example, a first gate metallization for connection to the HS switch
5 element 11 may be located at the side of the DC+ metallization 13a facing away from the AC metallization 15a. A second gate metallization for connection to the LS switch element 9 may be located adjacent to the AC metallization 15, e.g., between the DC+ metallization 13 and the AC
10 metallization 15. The second gate metallization may be alternatively located on the DC- metallization 14.

The relative arrangement of the further switch elements 9', 9'', 11', 11'' and further diodes 10', 10'', 12', 12'' is the
15 same but only shifted along the length direction L.

Figure 7 shows a further layout of a power module 1. In this embodiment, the DC-metallizations and associated terminals are not arranged in a '+/-/+'-scheme (from top to bottom in
20 the figure) but are arranged in a '-/+-'-'-scheme.

In this embodiment, the first switch element 9 and the first diode 10 are parts of the HS switch and the second switch element 11 and the second diode 12 are part of the LS switch.
25 Also here, the order of the sides (HS-LS-LS-HS) is the same when going from bottom to top or from top to bottom. The second switch element 11 and the second diode 12 are located close to each other on the same DC+ metallization 13 at different positions along the width direction W. The first
30 switch element 11 and the associated first diode 12 are arranged close to each other. However, the first switch element 9 and the associated diode 10 are separated from each other by the DC+ metallization 13 and the second switch

element 11 and the second diode 12. Also in this embodiment, the commutation path 16 from the second diode 12 via the first switch element 9 to the DC- metallization 14 and also the commutation path 17 from the second switch element 11 via the first diode 10 to the DC- metallization 14a is short and the inductance is low.

As in the previous embodiments, the first set of switch elements 9, 11 and associated diodes 10, 12 of the switches are arranged at the same positions along the length L of the power module 1. The second set of switch element 9', 11' and associated diodes 10', 12' is arranged identically but only shifted along the length direction L. Also the third set of switch elements 9'', 11'' and associated diodes 10'', 12'' is arranged identically but only shifted along the length direction L.

Figure 8 shows a further layout of a power module 1. In comparison to the layout of Figure 7, the positions of the second switch elements 11, 11', 11'' and the positions of the associated diodes 12, 12', 12'' are swapped. Also in this case, a balanced load and loss distribution can be obtained.

Figure 9 shows a further layout of a power module 1. In this embodiment, the DC-metallizations and associated terminals are arranged in a '-/+/-/+/-'-scheme along the width direction W.

The shown embodiment is obtained when the layout scheme shown in Figure 8 is doubled in the width direction W, with a shared DC- terminal 14a. Accordingly, the power module 1 comprises a first set of switches forming a half-bridge, the first set comprising first and second switch elements 9, 11

and associated diodes 10, 12 and a second set of switches comprising additional switch elements 9a, 11a and associated additional diodes 10a, 12a. Due to a separation of the respective metallizations within the power module 1, the
5 parallel connection may be established when the module terminal is further connected, to an inverter, for example.

Further sets of identically arranged switches are located at positions shifted along the longitudinal direction L,
10 exemplarily at regular distances from each other. Accordingly, the layout is symmetric in regard of the arrangement of the switch elements and diodes in a direction along the metallizations. Exemplarily, the switch elements and diodes of each side are merely shifted along the
15 metallization direction but the layout does not change along the metallization.

Simulations of the layout shown in Figure 3 show that mutual coupling inductances for each switch element between the
20 associated commutation loop and gate loop are negative and well-balanced and, thus, a proper dynamic current sharing can be accomplished. In addition to that, the switching behavior at a simulated turn-off of switch elements and turn-on on diodes for all three switch elements is well-aligned and,
25 thus, a good balance is accomplished between switch elements of the switches. Also the switching behavior of the diodes is well-balanced.

Reference Signs

	1	power module
	2	first switch
5	3	second switch
	4, 4'	DC+ terminal
	5	DC- terminal
	6	AC terminal
	7	first gate terminal
10	8	second gate terminal
	9	first switch element
	9', 9'', 9a	further first switch element
	10	first diode
	10', 10'', 10a	further first diode
15	11	second switch element
	11', 11'', 11a	further second switch element
	12	second diode
	12', 12'', 12a	further second diode
	13, 13a	DC+ metallization
20	14, 14a, 14b	DC- metallization
	15, 15a, 15b, 15c	AC metallization
	16	commutation path
	17	commutation path
	18	substrate
25	19	wire bond
	20, 20', 20''	gate
	21	first gate metallization
	22	second gate metallization
	23	first gate terminal
30	24	second gate terminal
	25	simulation result for embodiment
	26	simulation result for reference
	27	additional first switch element
	28	additional first diode

29 additional second switch element
30 additional second diode
31 metallization

5 U voltage
I current
W width direction
L length direction

Claims

1. A power module (1) comprising
- a first switch (2) comprising a first switch element (9)
 - 5 and an associated first diode (10),
 - a second switch (3) comprising a second switch element (11)
 - and an associated second diode (12),
 - the first switch (2) and the second switch (3) being
 - electrically connected to form a half-bridge,
 - 10 - metallizations (31) comprising one or more AC
 - metallizations (15, 15a, 15b, 15c), one or more DC+
 - metallizations (13, 13a) and one or more DC- metallizations
 - (14, 14a, 14b),
 - one or more AC terminals (6) connected to the AC
 - 15 metallizations (15, 15a, 15b, 15c), one or more DC+ terminals
 - (4, 4') connected to the DC+ metallizations (13, 13a) and one
 - or more DC- terminals (5) connected to the DC- metallizations
 - (14, 14a, 14b),
 - wherein at least one AC metallization (15, 15a, 15b, 15c) is
 - 20 located between at least one DC- metallization (14, 14a, 14b)
 - and at least one DC+ metallization (13, 13a),
 - wherein the first switch element (9), the second switch
 - element (11), the first diode (10) and the second diode (12)
 - are located next to each other and are located on the DC+
 - 25 metallizations (13, 13a) and AC metallizations (15, 15a, 15b,
 - 15c), wherein the second switch element (11) and the second
 - diode (12) are located between the first switch element (9)
 - and the first diode (10).
- 30 2. The power module (1) of claim 1,
- wherein the metallizations (31)() are arranged in the form of
- strips parallel to each other.

3. The power module (1) of any of the preceding claims,
comprising a gate metallization (21, 22) connected to a gate
(20) of the second switch element (11), wherein the gate
metallization (21, 22) has the form of a strip located
5 between the second switch element (11) and one of the first
diode (10) and the second diode (12) located next to the
second switch element (11).

4. The power module (1) of any of the preceding claims,
10 wherein the first switch (2) comprises one or more further
first switch elements (9', 9'') and associated further first
diodes (10', 10'') and the second switch (3) comprises one or
more further second switch elements (11', 11'') and
associated further second diodes (12', 12''), wherein the
15 first switch element (9) and the further first switch
elements (9', 9'') are located next to each other in a row,
the second switch element (11) and the further second switch
elements (11', 11'') are located next to each other in a row,
the first diode (10) and the further first diodes (10', 10'')
20 are located next to each other in a row and the second diode
(12) and the further second diodes (12', 12'') are located
next to each other in a row.

5. The power module (1) of claim 4,
25 wherein the first switch element (9) and the one or more
further first switch elements (9', 9'') are located on the
same one of the metallizations (31) and wherein the second
switch element (11) and the one or more further second switch
elements (11', 11'') are located on the same one of the
30 metallizations (31).

6. The power module (1) of any of the preceding claims, wherein the first switch element (9) is located next to the second diode (12) and the first diode (10) is located next to the second switch element (11).

5

7. The power module (1) of any of the preceding claims, wherein the first switch element (9) is located next to the second switch element (11) and the first diode (10) is located next to the second diode (12).

10

8. The power module (1) of any of the preceding claims, comprising at least three DC terminals in the form of at least one DC- terminal (5) and at least one DC+ terminal (4, 4'), the three DC terminals being located on one side of the power module (1) and having alternating polarity and comprising at least one AC terminal (6) located on an opposite side of the power module (1).

15

9. The power module (1) of any of the preceding claims, wherein the second diode (12) and the second switch element (11) are separated by one of the metallizations (31) on which the first and second switch elements (9, 11) and associated first and second diodes (10, 12) are located,.

20

10. The power module of any the preceding claims, comprising wherein the second switch element (11) and the second diode (12) are located on the same one of the metallizations (31).

25

11. The power module (1) of any of the preceding claims, wherein the second diode (12) is located closer to the first switch element (9) than to the second switch element (11).

30

12. The power module (1) of any of the preceding claims, wherein the first switch (9) is a low side switch connected to a DC- terminal (5) and the second switch (11) is a high side switch connected to a DC+ terminal (4, 4').

5

13. The power module (1) of any of claims 1 to 11, wherein the first switch (9) is a high side switch connected to a DC+ terminal (4, 4') and the second switch (11) is a low side switch connected to a DC- terminal (5).

10

14. The power module (1) of any of the preceding claims, comprising at least one additional first switch element (9a), associated additional first diode (10a), additional second switch element (11a) and associated additional second diode (12a) located in the same column as the first switch element (9), the second switch element (9), the first diode (19) and the second diode (12).

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15. The power module (1) of any of the preceding claims, wherein the first switch (2) comprises one or more further first switch elements (9', 9'') and the second switch (3) comprises one or more further second switch elements (11', 11''), wherein each of the first switch (2) and the second switch (3) has an odd number of switch elements (9, 9', 9'', 11, 11', 11'').

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Fig. 1

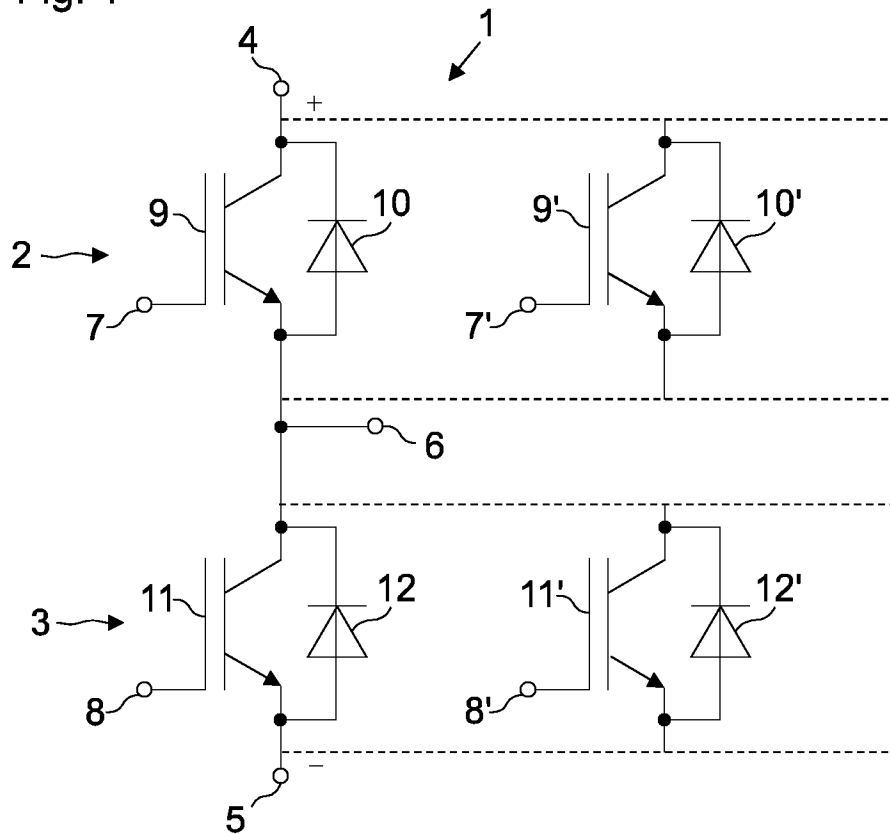
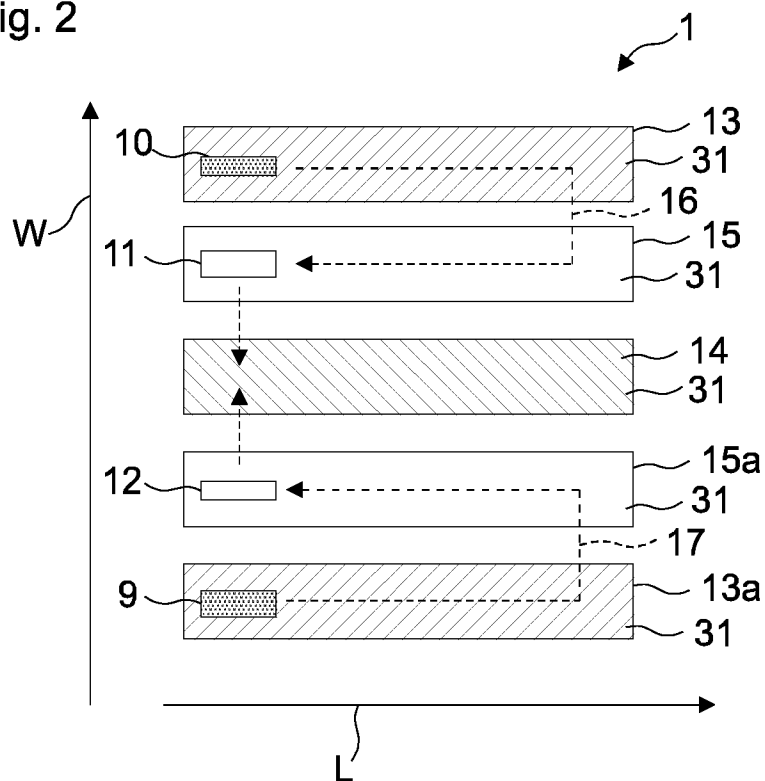
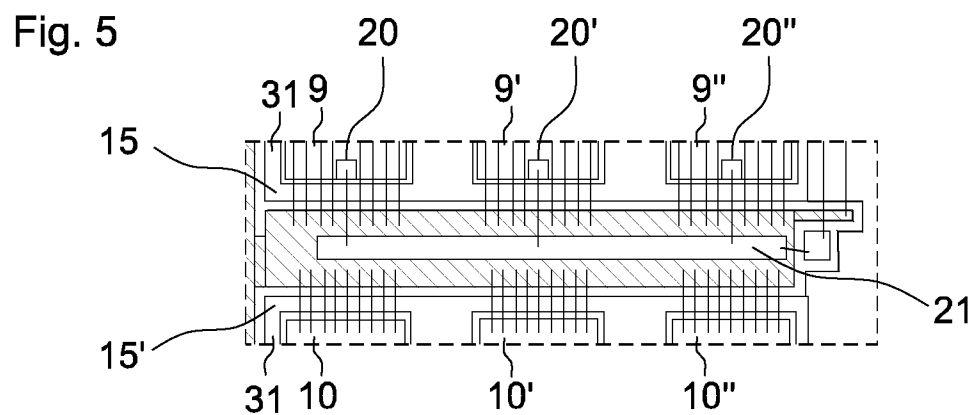
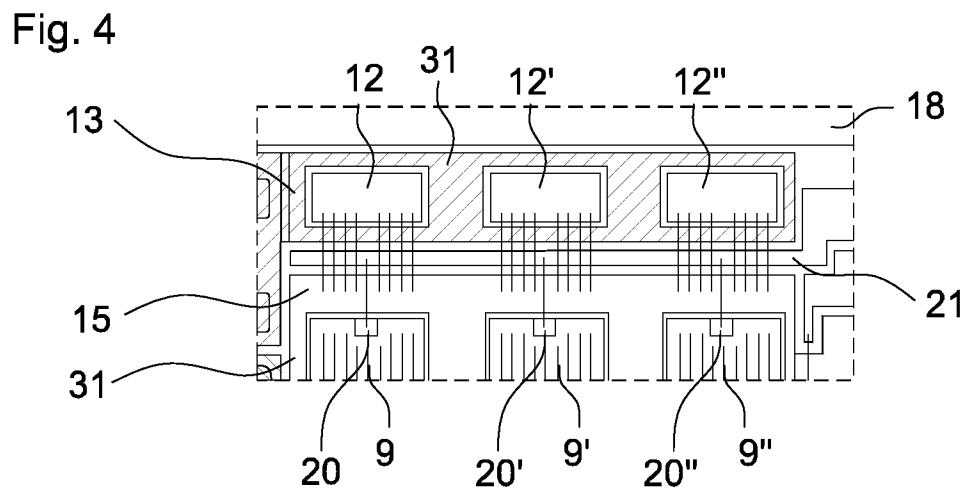
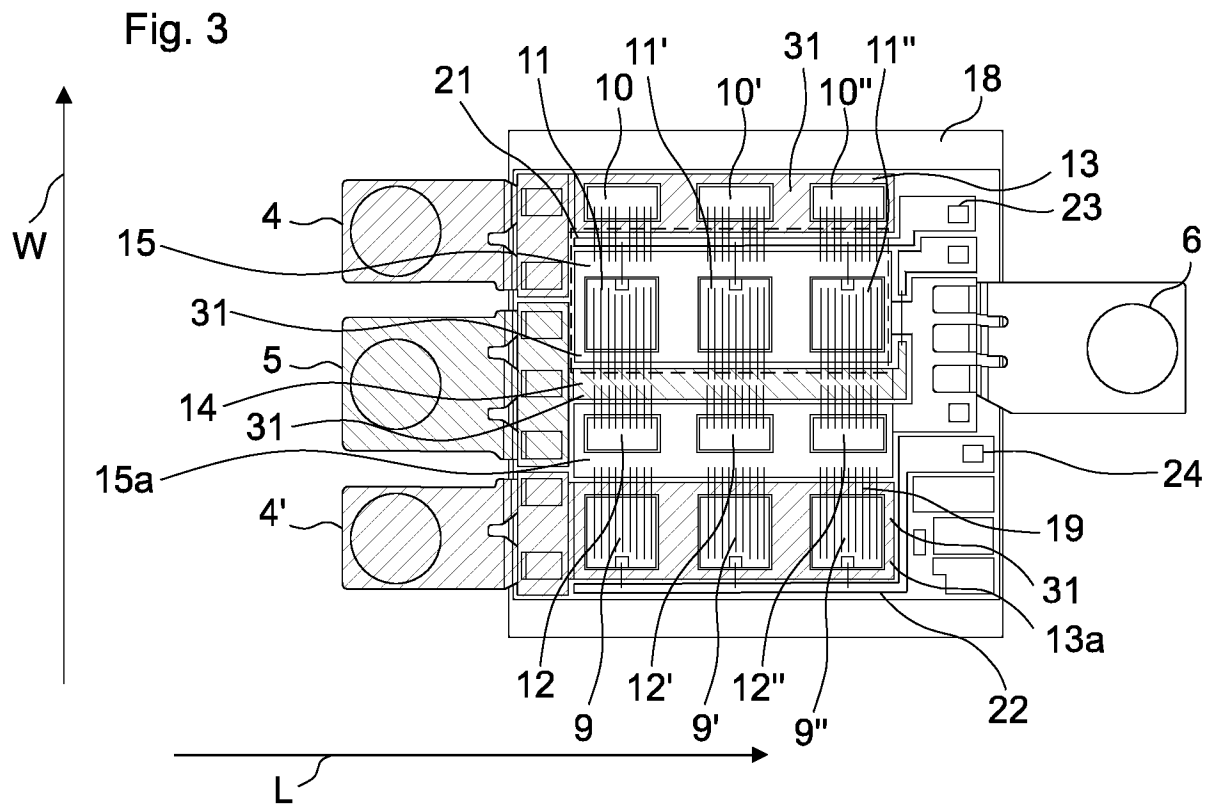


Fig. 2



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Fig. 6

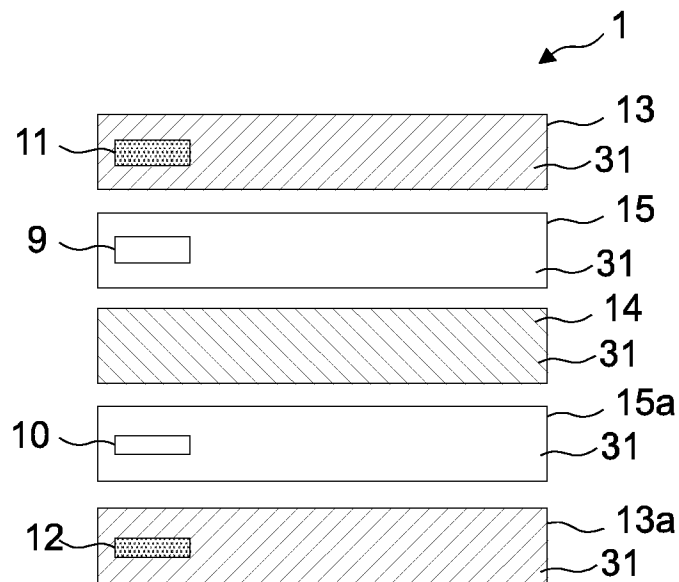
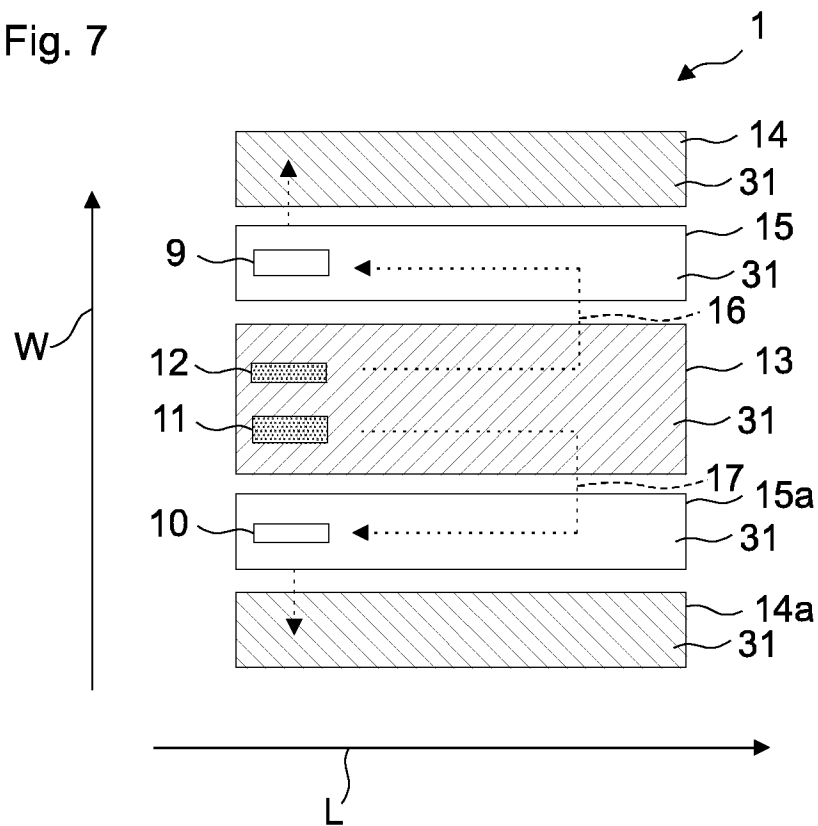


Fig. 7



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Fig. 8

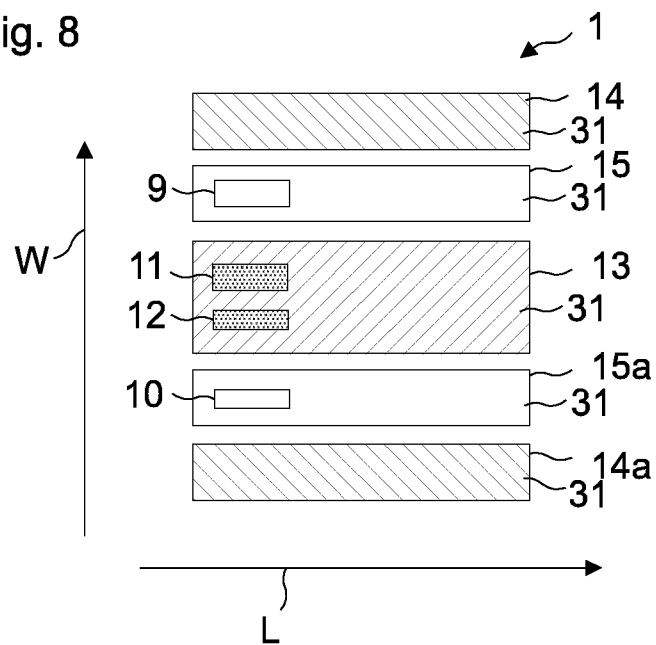
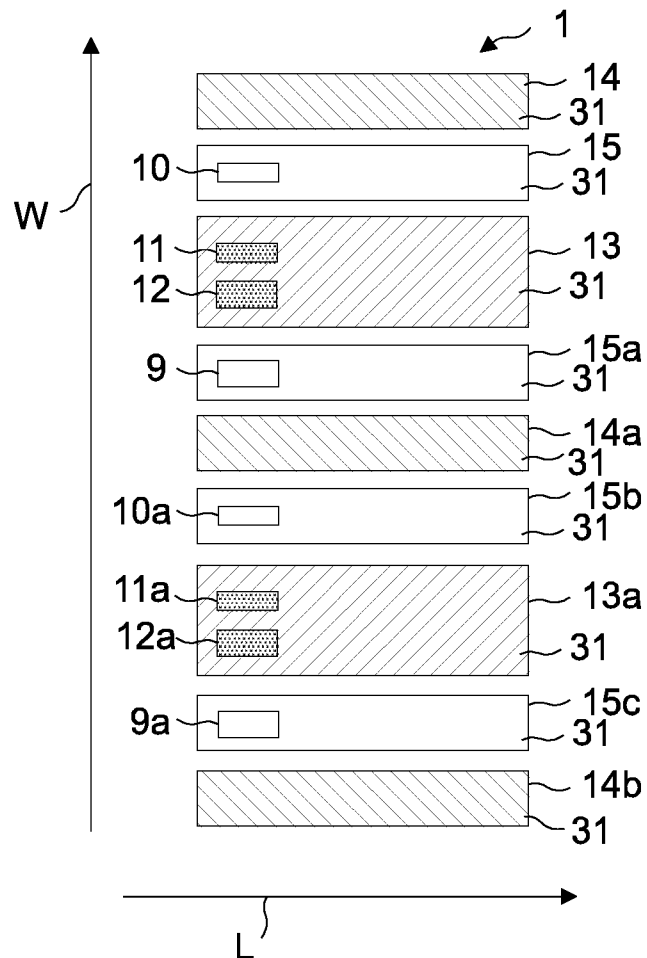


Fig. 9



INTERNATIONAL SEARCH REPORT

International application No

PCT/EP2022/057795

A. CLASSIFICATION OF SUBJECT MATTER

INV. H01L25/07 H01L25/18
ADD. H01L23/538

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	JP 2005 216876 A (FUJI ELEC DEVICE TECH CO LTD) 11 August 2005 (2005-08-11)	1, 6-13
Y	abstract; figures 1-22	4, 5, 15
A	-----	2, 3, 14
Y	EP 3 613 077 B1 (ABB POWER GRIDS SWITZERLAND AG [CH]; AUDI AG [DE]) 7 October 2020 (2020-10-07) paragraphs [0067] - [0081]; figures 1A, 1B figure 9	4, 5, 15
A	-----	1-15
	US 2011/062491 A1 (NAKATA SHUHEI [JP]) 17 March 2011 (2011-03-17) paragraphs [0067] - [0071]; figures 1, 2, 6, 7	

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Further documents are listed in the continuation of Box C.



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Date of the actual completion of the international search

8 July 2022

Date of mailing of the international search report

18/07/2022

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INTERNATIONAL SEARCH REPORT

International application No

PCT/EP2022/057795

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2018/190636 A1 (MUKUNOKI YASUSHIGE [JP] ET AL) 5 July 2018 (2018-07-05) paragraphs [0030] - [0065]; figures 1-5 -----	1-15
A	EP 2 631 946 A1 (SEMIKRON ELEKTRONIK GMBH [DE]) 28 August 2013 (2013-08-28) paragraph [0049]; figure 10 -----	1-15

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/EP2022/057795

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
JP 2005216876 A	11-08-2005	JP 4164810 B2 JP 2005216876 A	15-10-2008 11-08-2005
EP 3613077 B1	07-10-2020	CN 110785842 A EP 3613077 A1 JP 2020519024 A US 2020066686 A1 WO 2018202620 A1	11-02-2020 26-02-2020 25-06-2020 27-02-2020 08-11-2018
US 2011062491 A1	17-03-2011	CN 102067309 A DE 112009001638 T5 JP 5550553 B2 JP WO2010004802 A1 KR 20110020294 A US 2011062491 A1 WO 2010004802 A1	18-05-2011 19-05-2011 16-07-2014 22-12-2011 02-03-2011 17-03-2011 14-01-2010
US 2018190636 A1	05-07-2018	CN 107851637 A DE 112016003111 T5 JP 6400201 B2 JP WO2017006809 A1 US 2018190636 A1 WO 2017006809 A1	27-03-2018 12-04-2018 03-10-2018 24-05-2018 05-07-2018 12-01-2017
EP 2631946 A1	28-08-2013	CN 103296016 A CN 203165891 U DE 102012202765 B3 EP 2631946 A1 JP 6047423 B2 JP 2013175727 A KR 20130097107 A	11-09-2013 28-08-2013 18-04-2013 28-08-2013 21-12-2016 05-09-2013 02-09-2013